

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

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Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SA1122

Silicon PNP Epitaxial

RENESAS

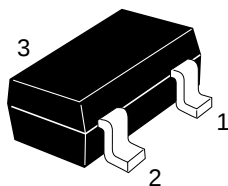
ADE-208-1009 (Z)
1st. Edition
Mar. 2001

Application

Low frequency amplifier

Outline

MPAK



- 1. Emitter
- 2. Base
- 3. Collector

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	−55	V
Collector to emitter voltage	V _{CEO}	−55	V
Emitter to base voltage	V _{EBO}	−5	V
Collector current	I _C	−100	mA
Collector power dissipation	P _C	150	mW
Junction temperature	T _j	150	°C
Storage temperature	T _{stg}	−55 to +150	°C

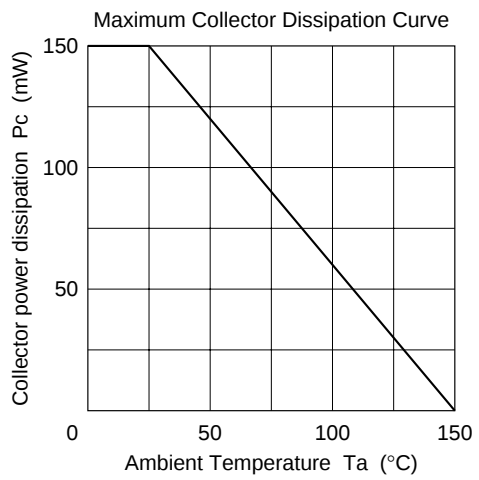
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	V _{(BR)CBO}	−55	—	—	V	I _C = −10 μA, I _E = 0
Collector to emitter breakdown voltage	V _{(BR)CEO}	−55	—	—	V	I _C = −1 mA, R _{BE} = ∞
Emitter to base breakdown voltage	V _{(BR)EBO}	−5	—	—	V	I _E = −10 μA, I _C = 0
Collector cutoff current	I _{CBO}	—	—	−0.5	μA	V _{CB} = −30 V, I _E = 0
Emitter cutoff current	I _{EBO}	—	—	−0.5	μA	V _{EB} = −2 V, I _C = 0
DC current transfer ratio	h _{FE} ^{*1}	160	—	800		V _{CE} = −12 V, I _C = −2 mA
Collector to emitter saturation voltage	V _{CE(sat)}	—	—	−0.5	V	I _C = −10 mA, I _B = −1 mA
Base to emitter voltage	V _{BE}	—	—	−0.75	V	V _{CE} = −12 V, I _C = −2 mA

Note: 1. The 2SA1122 is grouped by h_{FE} as follows.

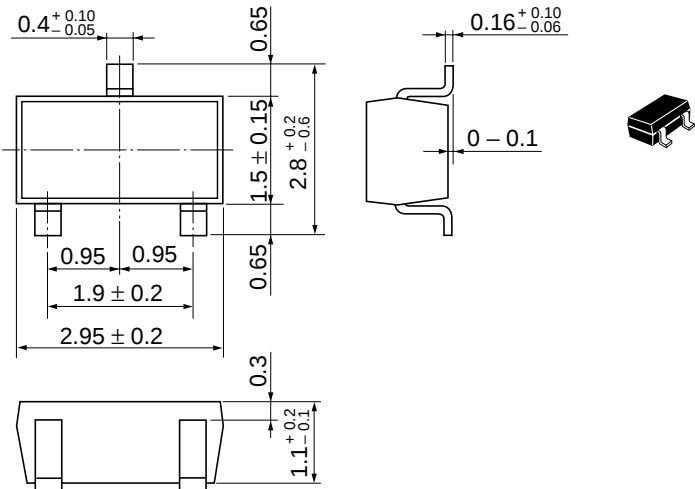
Grade	B	C	D
Mark	CC	CD	CE
h _{FE}	160 to 320	250 to 500	400 to 800

See characteristic curves of 2SA836.



Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	MPAK
JEDEC	—
EIAJ	Conforms
Mass (reference value)	0.011 g

Cautions

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